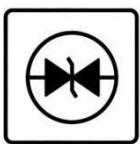




ESD



TVS



TSS



MOV



GDT



PLED

BSC070N10NS5-MS

Product specification

Description

The BSC070N10NS5-MS use advanced SGT MOSFET technology to provide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics. This device is specially designed to get better ruggedness and suitable.

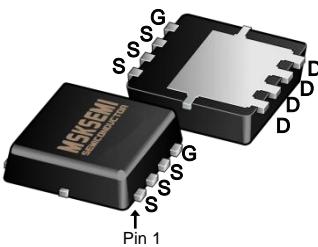
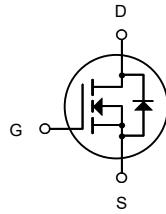
Features

- $V_{DS} = 100V$ $I_D = 75A$
- $R_{DS(ON)} < 9.2m\Omega$ @ $V_{GS} = 10V$

Application

- Consumer electronic power supply Motor control
- Synchronous-rectification Isolated DC
- Synchronous-rectification applications

Reference News

DFN5X6-8L	N-Channel MOSFET	Marking
		

Absolute Maximum Ratings

at $T_j = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	100	V
Gate source voltage	V_{GS}	± 20	V
Continuous drain current ¹⁾	I_D	75	A
Pulsed drain current ²⁾	I_D , pulse	300	A
Power dissipation ³⁾	P_D	97	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	90	mJ
Operation and storage temperature	T_{STG}, T_j	-55 to 150	°C
Thermal resistance, junction-case	$R_{\theta JC}$	1.3	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_D=250\mu\text{A}$	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=100\text{V}$, $V_{\text{GS}}=0\text{V}$,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{\text{DS}}=0\text{V}$, $V_{\text{GS}}= \pm 20\text{V}$	-	-	± 100	nA
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$, $I_D=250\mu\text{A}$	1.0	1.6	2.5	V
$R_{\text{DS}(\text{on})}$	Static Drain-Source on-Resistance note3	$V_{\text{GS}}=10\text{V}$, $I_D=20\text{A}$	-	7.3	9.2	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}$, $I_D=8\text{A}$	-	9	13.5	$\text{m}\Omega$
C_{iss}	Input Capacitance	$V_{\text{DS}}=50\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1.0\text{MHz}$	-	2046	-	pF
C_{oss}	Output Capacitance		-	865	-	pF
C_{rss}	Reverse Transfer Capacitance		-	25	-	pF
Q_g	Total Gate Charge	$V_{\text{DS}}=50\text{V}$, $I_D=30\text{A}$, $V_{\text{GS}}=10\text{V}$	-	39.4	-	nC
Q_{gs}	Gate-Source Charge		-	5.2	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	9.8	-	nC
$t_{\text{d}(\text{on})}$	Turn-on Delay Time	$V_{\text{DD}}=50\text{V}$, $I_D=25\text{A}$, $R_G=6\Omega$, $V_{\text{GS}}=10\text{V}$	-	20	-	ns
t_r	Turn-on Rise Time		-	5.2	-	ns
$t_{\text{d}(\text{off})}$	Turn-off Delay Time		-	49	-	ns
t_f	Turn-off Fall Time		-	12	-	ns
I_s	Maximum Continuous Drain to Source Diode Forward Current		-	-	75	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	300	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{\text{GS}}=0\text{V}$, $I_s=30\text{A}$	-	-	1	V
t_{rr}	Body Diode Reverse Recovery Time	$T_J=25^\circ\text{C}$, $I=12\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$	-	49	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	85	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: $T_J=25^\circ\text{C}$, $V_{\text{DD}}=50\text{V}$, $V_G=10\text{V}$, $R_G=25\Omega$, $L=0.5\text{mH}$, $I_{\text{AS}}=19\text{A}$
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

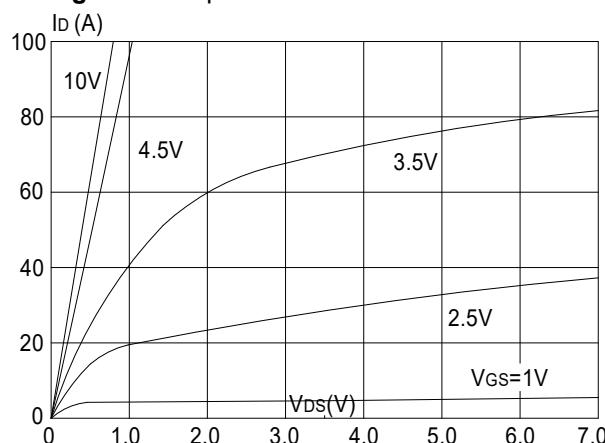


Figure 2: Typical Transfer Characteristics

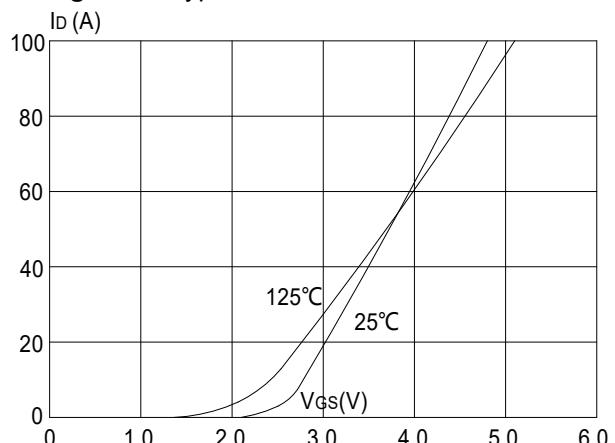


Figure 3: On-resistance vs. Drain Current

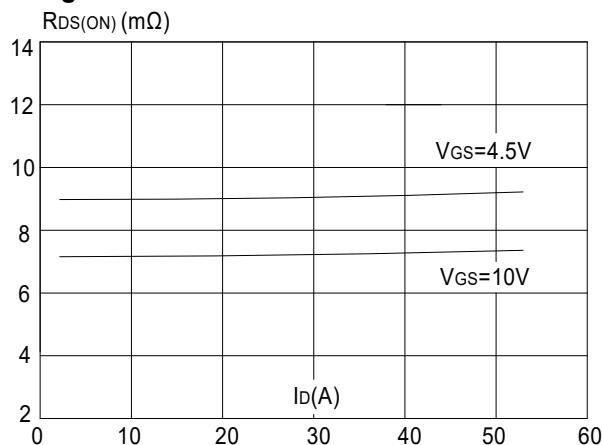


Figure 4: Body Diode Characteristics

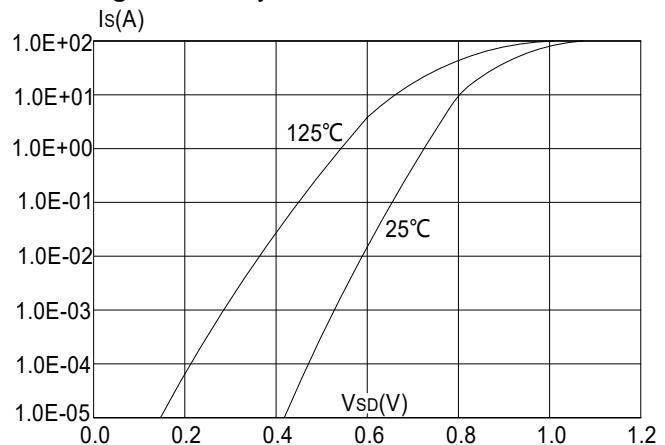


Figure 5: Gate Charge Characteristics

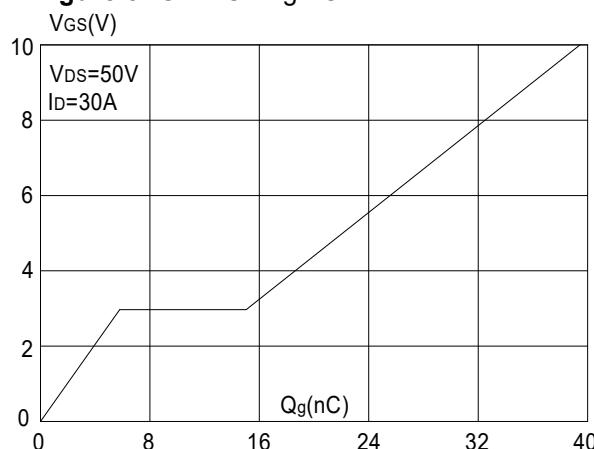


Figure 6: Capacitance Characteristics

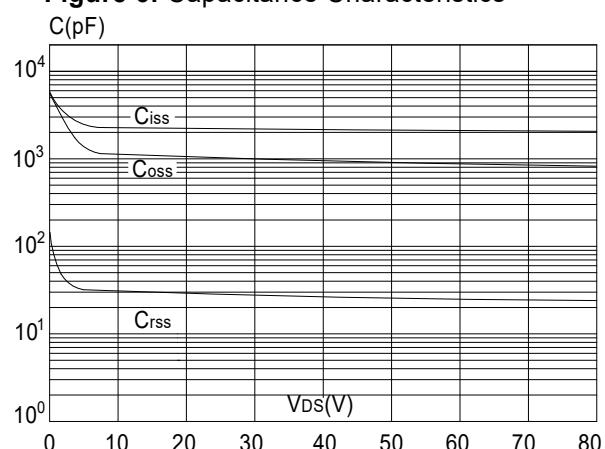


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

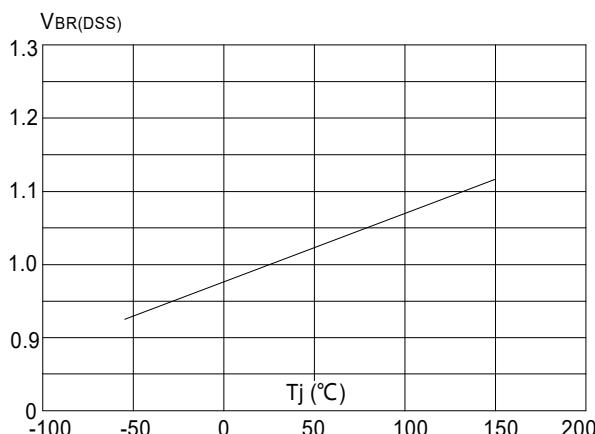


Figure 8: Normalized on Resistance vs. Junction Temperature

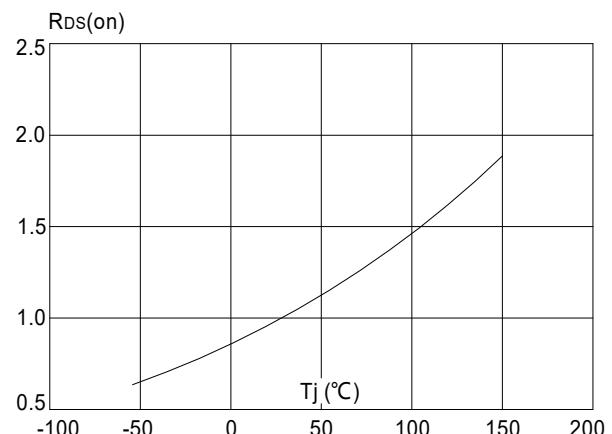


Figure 9: Maximum Safe Operating Area

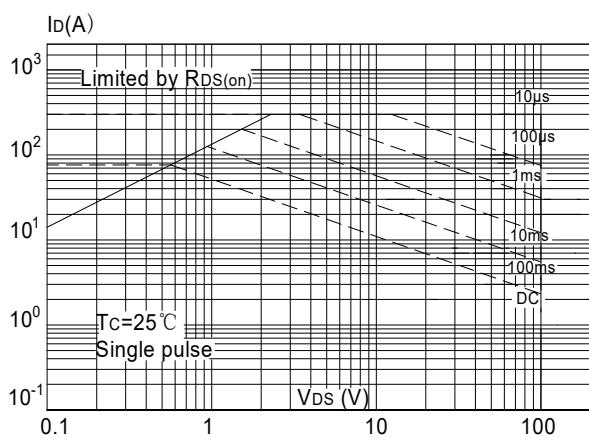


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

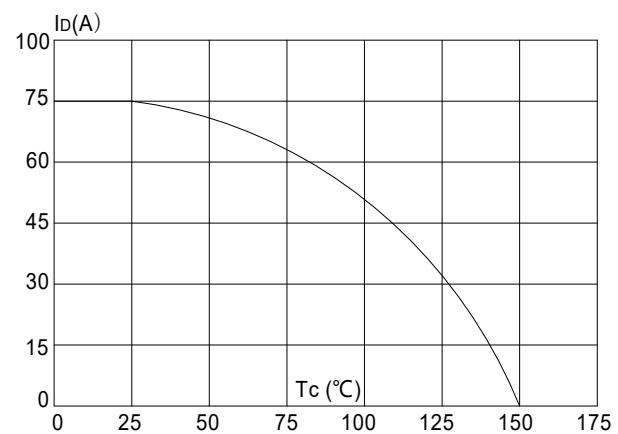
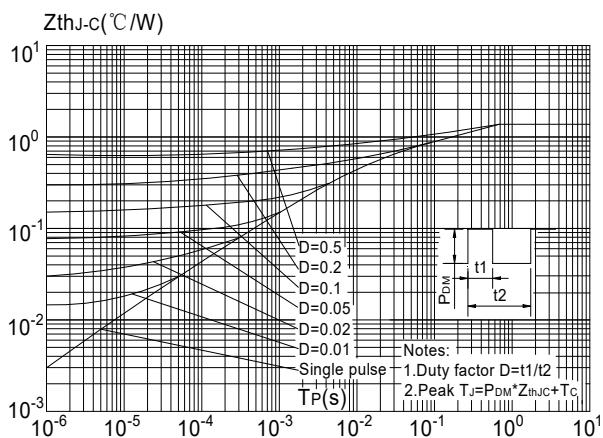


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuit

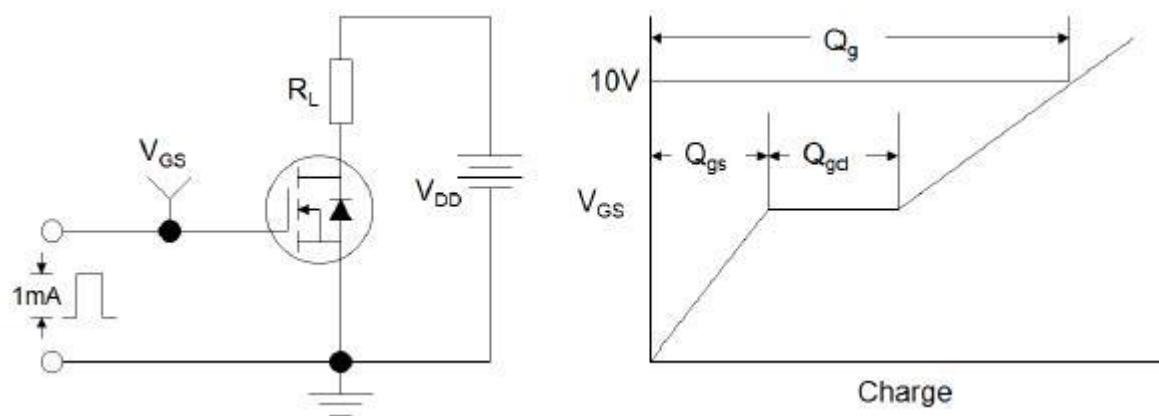


Figure1:Gate Charge Test Circuit & Waveform

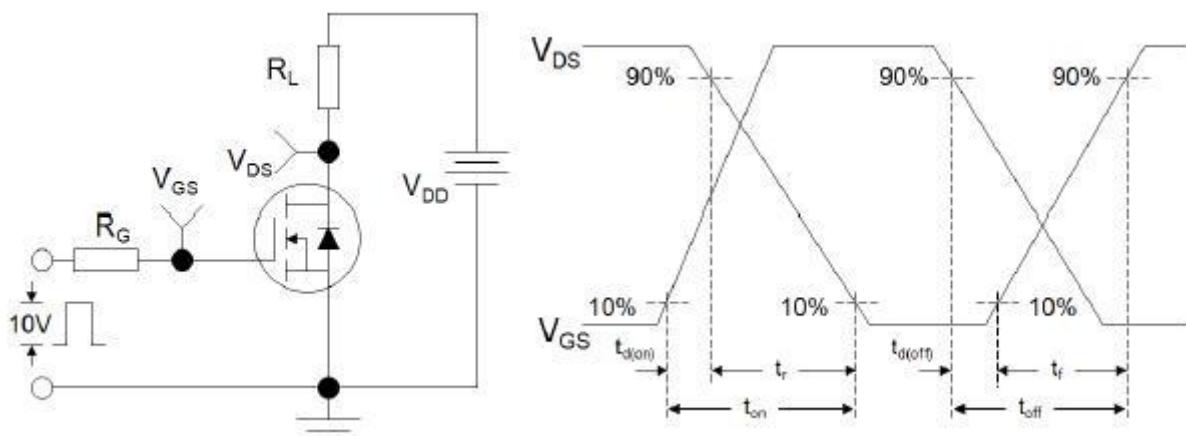


Figure 2: Resistive Switching Test Circuit & Waveforms

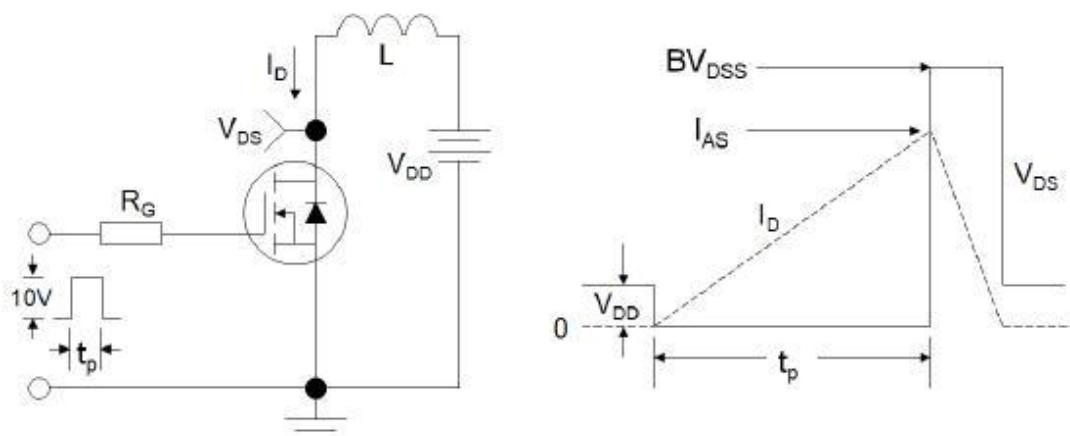
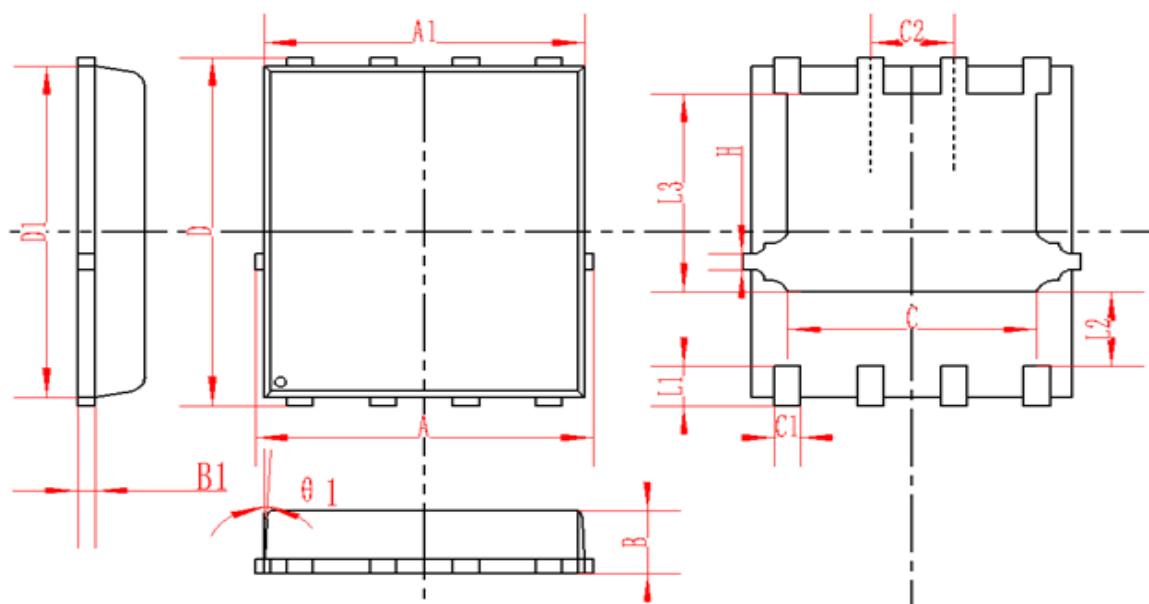


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

DFN5X6-8L Package Information


SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010

REEL SPECIFICATION

P/N	PKG	QTY
BSC070N10NS5-MS	DFN5X6-8L	5000

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